



2.5V DRIVE SILICON N-CHANNEL MOSFET

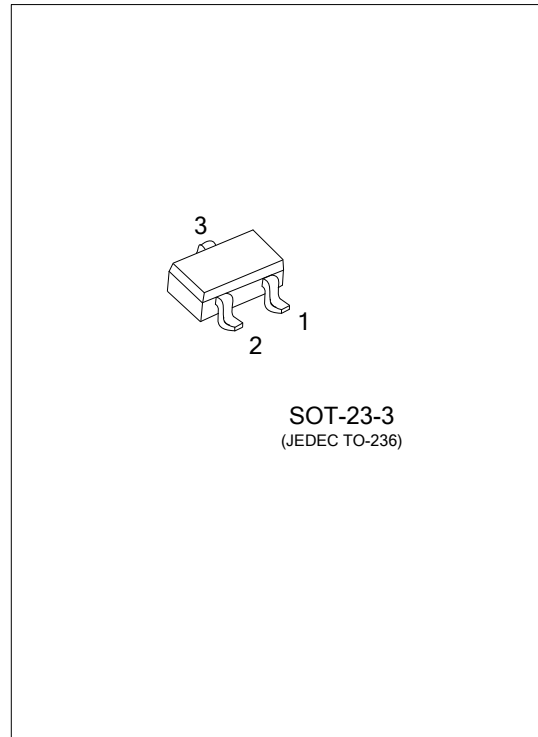
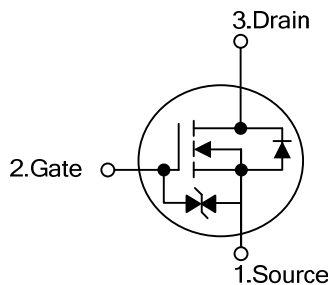
DESCRIPTION

The UTC **UK3019** is a silicon N-channel MOSFET which has been designed to minimize on-state resistance while it provides rugged, reliable and fast switching performance. The product is particularly suited for low voltage, low current applications such as small servo motor controller, power MOSFET gate drivers, and other switching applications.

FEATURES

- * Min $V_{DSS} = 30V$
- * $R_{DS(ON)} = 5\Omega (V_{GS}=4V)$
- * $R_{DS(ON)} = 7\Omega (V_{GS}=2.5V)$
- * Pulsed $I_D = 400mA$
- * Low Voltage Drive (2.5V)

SYMBOL

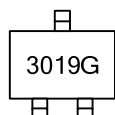


ORDERING INFORMATION

Ordering Number	Package	Pin Assignment			Packing
		1	2	3	
UK3019G-AE2-R	SOT-23-3	S	G	D	Tape Reel

<p>UK3019G-AE2-R</p> <ul style="list-style-type: none"> (1) Packing Type (2) Package Type (3) Halogen Free 	<ul style="list-style-type: none"> (1) R: Tape Reel (2) AE2: SOT-23-3 (3) G: Halogen Free
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MARKING



■ ABSOLUTE MAXIMUM RATING (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V _{DSS}	30	V
Gate-Source Voltage	V _{GSS}	±20	V
Drain Current	Continuous	I _D	100
	Pulsed (Note 2)	I _{DP}	400
Power Dissipation (Note 3)	P _D	200	mW
Junction Temperature	T _J	+150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Pw ≤ 10μs, Duty cycle ≤ 50%

3. With each pin mounted on the recommended lands.

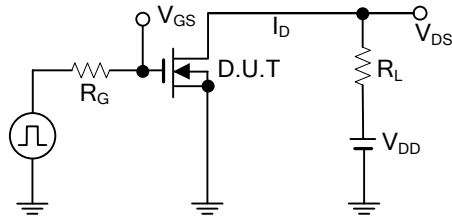
■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ _{JA}	625	°C/W

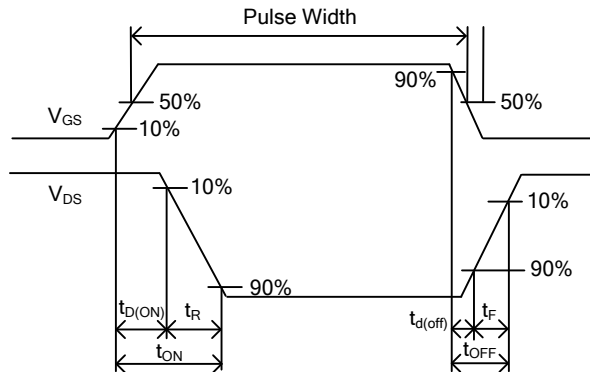
■ ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =10μA	30			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V			1.0	μA
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±1	μA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =3V, I _D =100μA	0.8		1.5	V
Static drain-source on-state resistance	R _{DS(ON)}	I _D = 10mA, V _{GS} = 4V		5	8	Ω
		I _D = 1mA, V _{GS} = 2.5V		7	13	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}	V _{DS} =5V, V _{GS} =0V, f = 1MHz		13		pF
Output Capacitance	C _{OSS}			9		pF
Reverse Transfer Capacitance	C _{RSS}			4		pF
SWITCHING PARAMETERS						
Turn-ON Delay Time	t _{D(ON)}	V _{GS} = 5V, V _{DD} ≈ 5V I _D = 10mA, R _L = 500Ω, R _G = 10Ω		15		ns
Turn-ON Rise Time	t _R			35		ns
Turn-OFF Delay Time	t _{D(OFF)}			80		ns
Turn-OFF Fall-Time	t _F			80		ns

■ TEST CIRCUITS AND WAVEFORMS



Switching Time Measurement Circuit



Switching Time Waveforms

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